

Thyristor T553-800-44



Mean on-state current	I_{TAV}		800 A		
Repetitive peak off-state voltage	V_{DRM}		3600 - 4400 V		
Repetitive peak reverse voltage	V_{RRM}				
Turn-off time	t_q		500, 630, 800 μ s		
V_{DRM}, V_{RRM}, V	3600	3800	4000	4200	4400
Voltage code	36	38	40	42	44
$T_j, ^\circ C$	-60 ÷ 125				

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions
ON-STATE				
I_{TAV}	Mean on-state current	A	800 847	$T_c=88^\circ C$, Double side cooled $T_c=85^\circ C$, Double side cooled 180° half-sine wave; 50 Hz
I_{TRMS}	RMS on-state current	A	1256	$T_c=88^\circ C$, Double side cooled 180° half-sine wave; 50 Hz
I_{TSM}	Surge on-state current	kA	16.0 18.0	$T_j=T_{jmax}$ $T_j=25^\circ C$ 180° half-sine wave; $t_p=10$ ms; single pulse; $V_D=V_R=0$ V; Gate pulse: $I_G=2$ A; $t_{GP}=50$ ms; $di_G/dt \geq 1$ A/ms
			17.0 20.0	$T_j=T_{jmax}$ $T_j=25^\circ C$ 180° half-sine wave; $t_p=8.3$ ms; single pulse; $V_D=V_R=0$ V; Gate pulse: $I_G=2$ A; $t_{GP}=50$ ms; $di_G/dt \geq 1$ A/ms
I^2t	Safety factor	$A^2s \cdot 10^3$	1200 1600	$T_j=T_{jmax}$ $T_j=25^\circ C$ 180° half-sine wave; $t_p=10$ ms; single pulse; $V_D=V_R=0$ V; Gate pulse: $I_G=2$ A; $t_{GP}=50$ ms; $di_G/dt \geq 1$ A/ms
			1100 1600	$T_j=T_{jmax}$ $T_j=25^\circ C$ 180° half-sine wave; $t_p=8.3$ ms; single pulse; $V_D=V_R=0$ V; Gate pulse: $I_G=2$ A; $t_{GP}=50$ ms; $di_G/dt \geq 1$ A/ms
BLOCKING				
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	3600 - 4400	$T_{jmin} < T_j < T_{jmax}$; 180° half-sine wave; 50 Hz; Gate open
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	3700 - 4500	$T_{jmin} < T_j < T_{jmax}$; 180° half-sine wave; single pulse; Gate open
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6 \cdot V_{DRM}$ $0.6 \cdot V_{RRM}$	$T_j=T_{jmax}$; Gate open

TRIGGERING				
I_{FGM}	Peak forward gate current	A	8	$T_j = T_{j\ max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	4	$T_j = T_{j\ max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/ms	1000	$T_j = T_{j\ max}$; $V_D = 0.67 \cdot V_{DRM}$; $I_{TM} = 2400$ A; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ ms; $di_G/dt \geq 2$ A/ms
THERMAL				
T_{stg}	Storage temperature	°C	-60...50	
T_j	Operating junction temperature	°C	-60...125	
MECHANICAL				
F	Mounting force	kN	24.0...28.0	
a	Acceleration	m/s ²	50	Device clamped

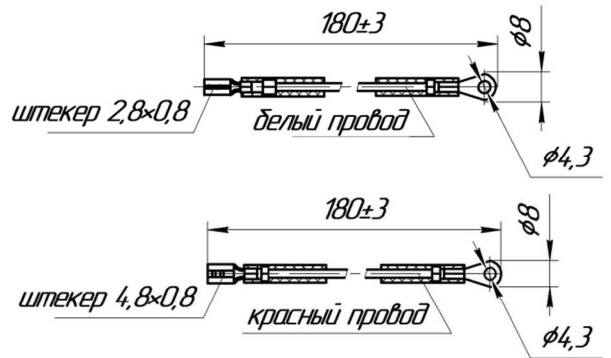
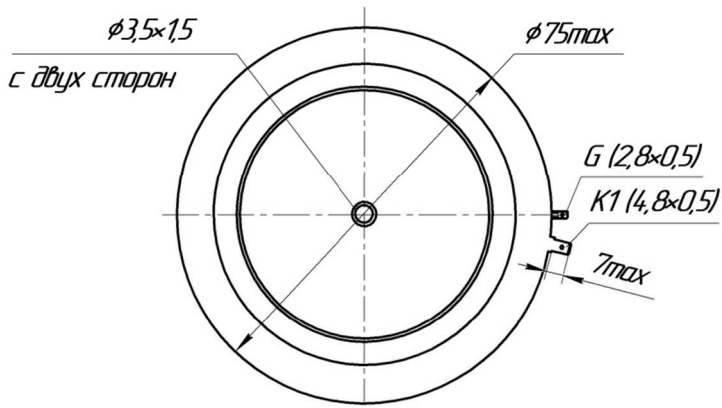
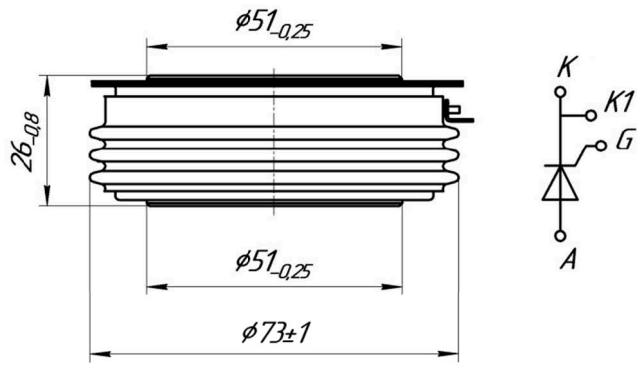
CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{TM}	Peak on-state voltage, max	V	2.60	$T_j = 25$ °C; $I_{TM} = 2512$ A	
$V_{T(TO)}$	On-state threshold voltage, max	V	1.144	$T_j = T_{j\ max}$;	
r_T	On-state slope resistance, max	mW	0.713	$0.5 \text{ p } I_{TAV} < I_T < 1.5 \text{ p } I_{TAV}$	
I_L	Latching current, max	mA	1500	$T_j = 25$ °C; $V_D = 12$ V; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ ms; $di_G/dt \geq 1$ A/ms	
I_H	Holding current, max	mA	300	$T_j = 25$ °C; $V_D = 12$ V; Gate open	
BLOCKING					
I_{DRM}, I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	150	$T_j = T_{j\ max}$; $V_D = V_{DRM}$; $V_R = V_{RRM}$	
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage ¹⁾ , min	V/ms	200, 320, 500, 1000, 1600, 2000, 2500	$T_j = T_{j\ max}$; $V_D = 0.67 \cdot V_{DRM}$; Gate open	
TRIGGERING					
V_{GT}	Gate trigger direct voltage, max	V	3.00	$T_j = T_{j\ min}$ $T_j = 25$ °C $T_j = T_{j\ max}$	$V_D = 12$ V; $I_D = 3$ A; Direct gate current
			2.50		
			1.50		
I_{GT}	Gate trigger direct current, max	mA	400	$T_j = T_{j\ min}$ $T_j = 25$ °C $T_j = T_{j\ max}$	
			250		
			150		
V_{GD}	Gate non-trigger direct voltage, min	V	0.35	$T_j = T_{j\ max}$; $V_D = 0.67 \cdot V_{DRM}$; Direct gate current	
I_{GD}	Gate non-trigger direct current, min	mA	40.00		
SWITCHING					
t_{gd}	Delay time, max	ms	2.75	$T_j = 25$ °C; $V_D = 1500$ V; $I_{TM} = I_{TAV}$; $di/dt = 200$ A/ms;	
t_{gt}	Turn-on time, max	ms	16.0	Gate pulse: $I_G = 2$ A; $V_G = 20$ V; $t_{GP} = 50$ ms; $di_G/dt = 2$ A/ms	
t_q	Turn-off time ²⁾ , max	ms	500, 630, 800	$dv_D/dt = 50$ V/ms; $T_j = T_{j\ max}$; $I_{TM} = I_{TAV}$; $di_R/dt = -5$ A/ms; $V_R = 100$ V; $V_D = 0.67 \cdot V_{DRM}$	
Q_{rr}	Total recovered charge, max	mC	3300	$T_j = T_{j\ max}$; $I_{TM} = 800$ A; $di_R/dt = -5$ A/ms; $V_R = 100$ V;	
t_{rr}	Reverse recovery time, max	ms	55		
I_{rrM}	Peak reverse recovery current, max	A	120		

THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0180	Direct current	Double side cooled
R_{thjc-A}			0.0396		Anode side cooled
R_{thjc-K}			0.0324		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0040	Direct current	
MECHANICAL					
w	Weight, max	g	550		
D_s	Surface creepage distance	mm (inch)	30.38 (1.196)		
D_a	Air strike distance	mm (inch)	18.05 (0.710)		

OVERALL DIMENSIONS

Package type: PT53



- K – cathode;
- A – anode;
- K1 – auxiliary cathode;
- G – gate;

All dimensions in millimeters

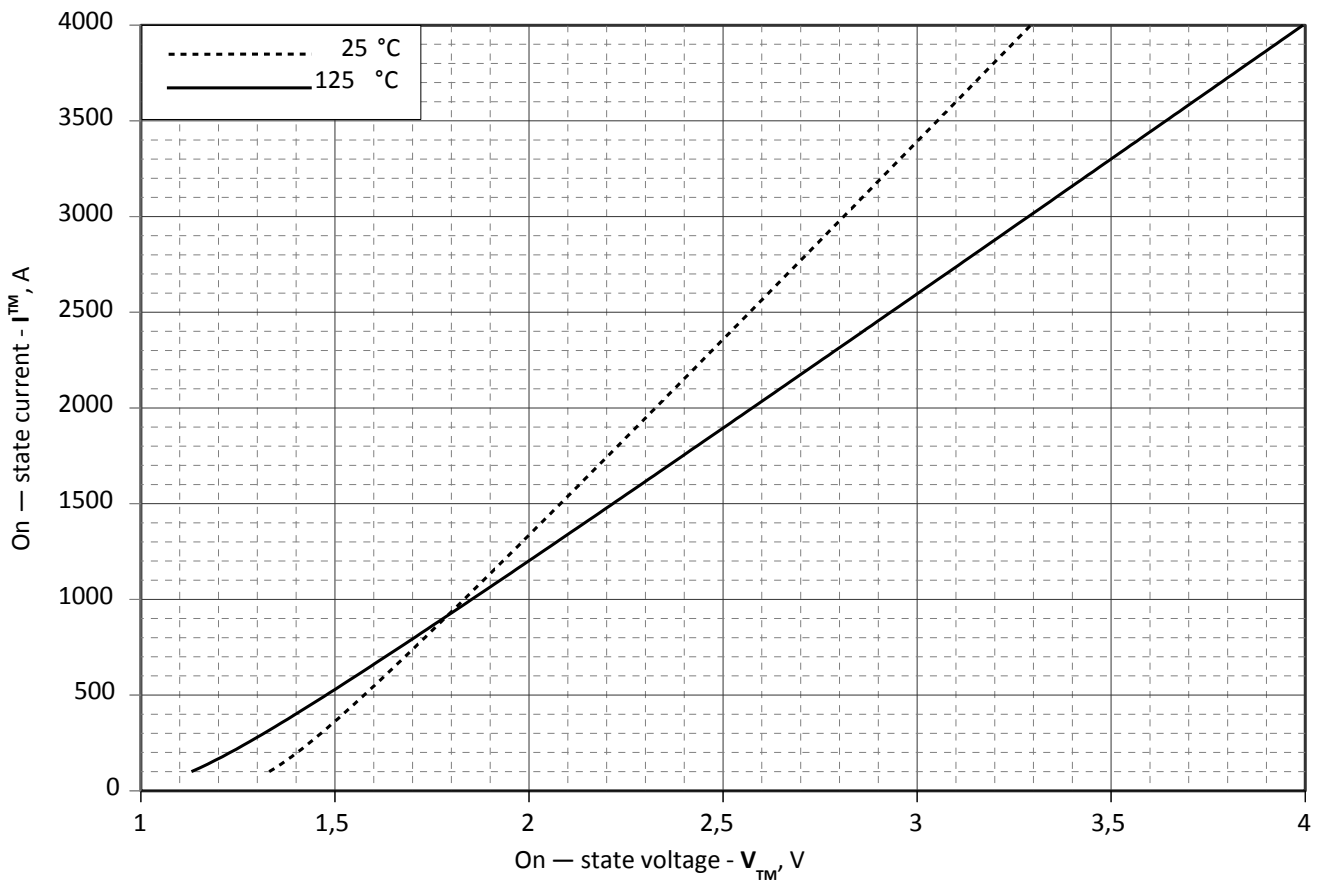


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j\max}$
A	1.09600000	0.84157000
B	0.00048225	0.00070287
C	0.04364400	0.04978800
D	-0.00148650	-0.00113010

On-state characteristic model (see Fig. 1)

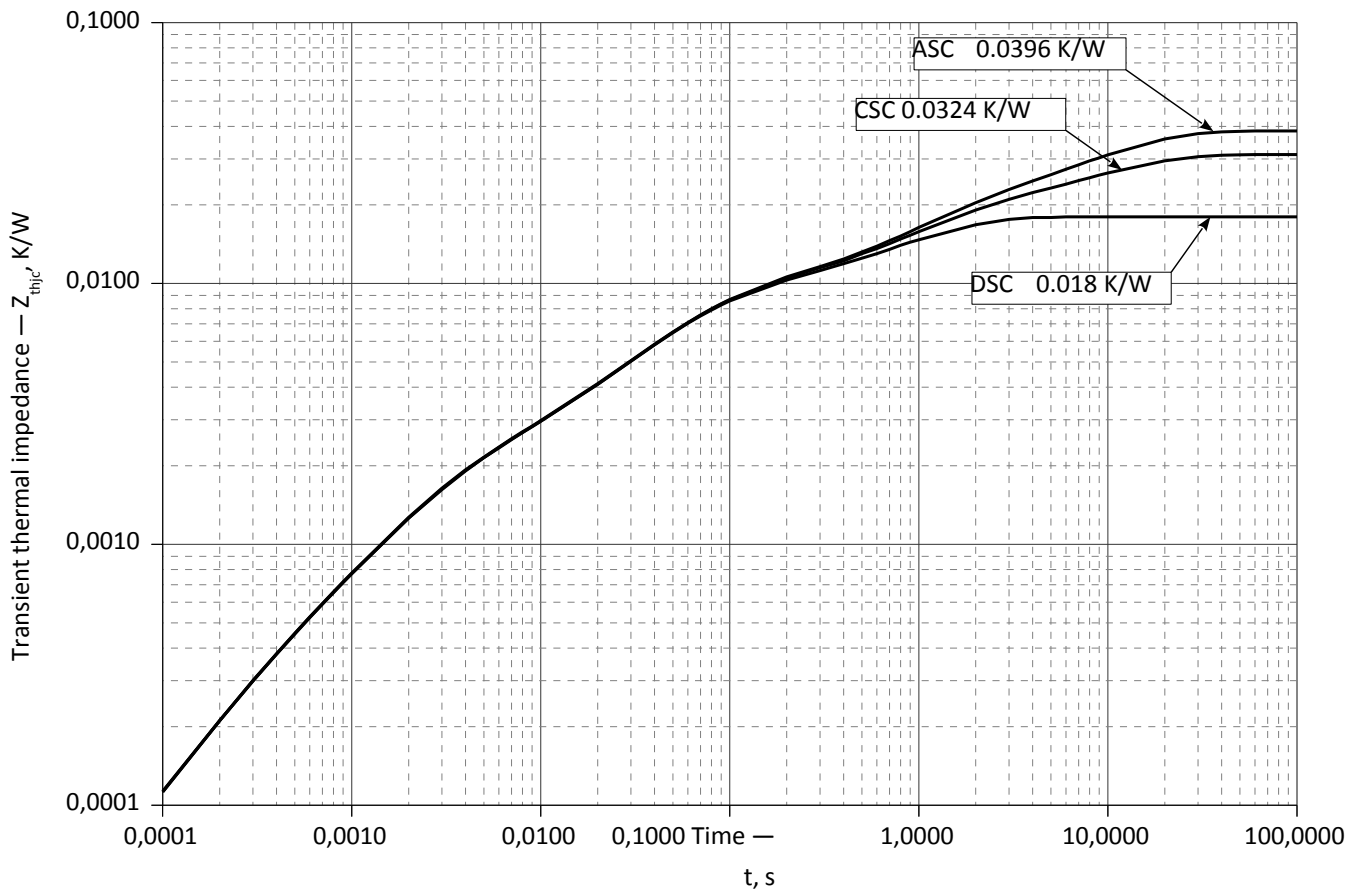


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i , K/W	0.009241	0.006037	0.001231	0.001054	0.0003396	0.00009575
τ_i , s	0.9673	0.04967	0.002733	0.07734	0.001638	0.0002248

DC Anode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.01318	0.009281	0.006055	0.001018	0.001535	0.0001182
τ_i , s	9.745	1.028	0.05591	0.03732	0.002468	0.0002687

DC Cathode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.02041	0.009325	0.006949	0.0001252	0.001516	0.0001119
τ_i , s	9.752	1.065	0.05344	0.01407	0.002421	0.0002554

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

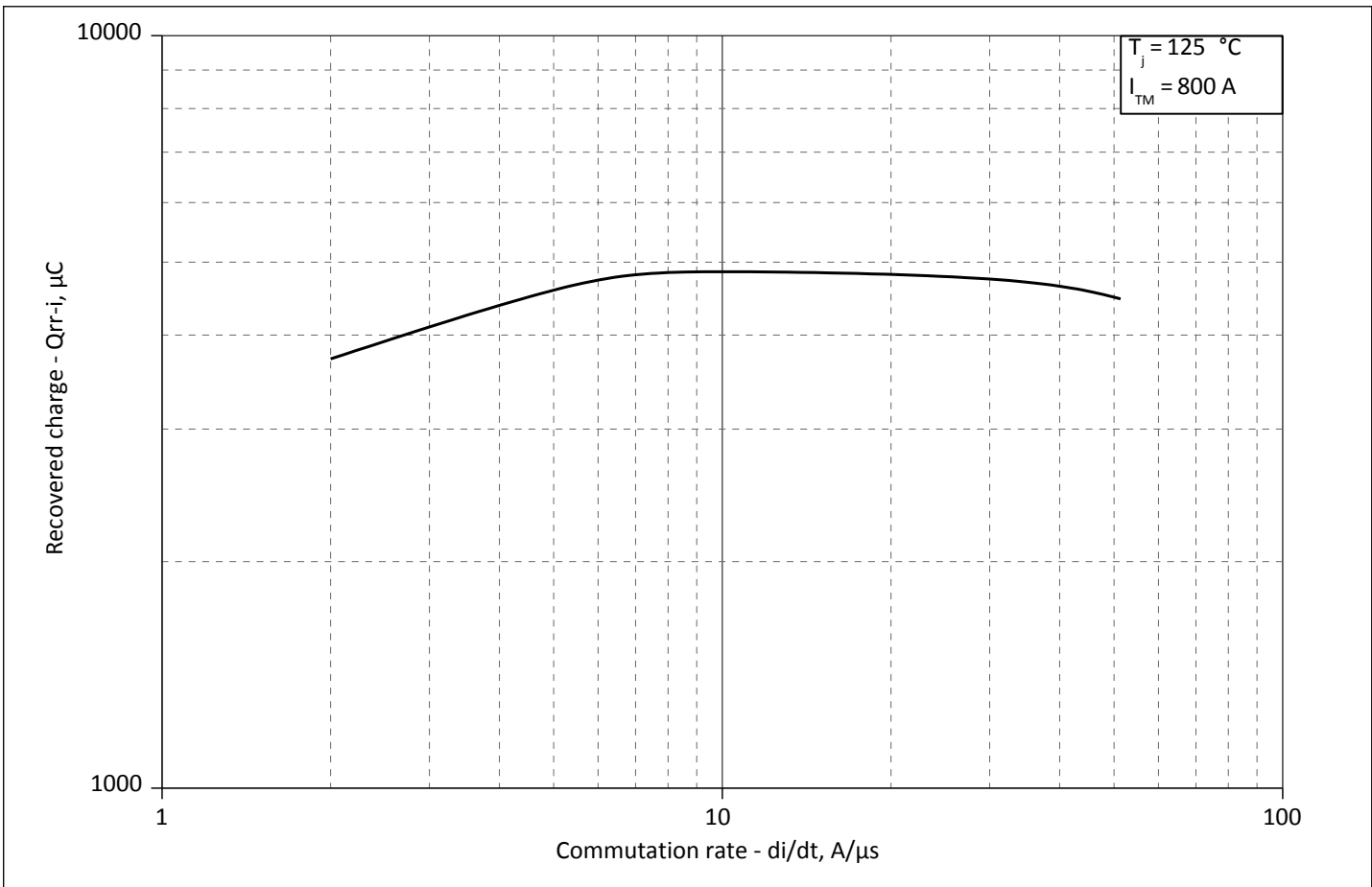


Fig 3 – Maximum recovered charge Q_{rr-i} (integral) vs. commutation rate di_r/dt

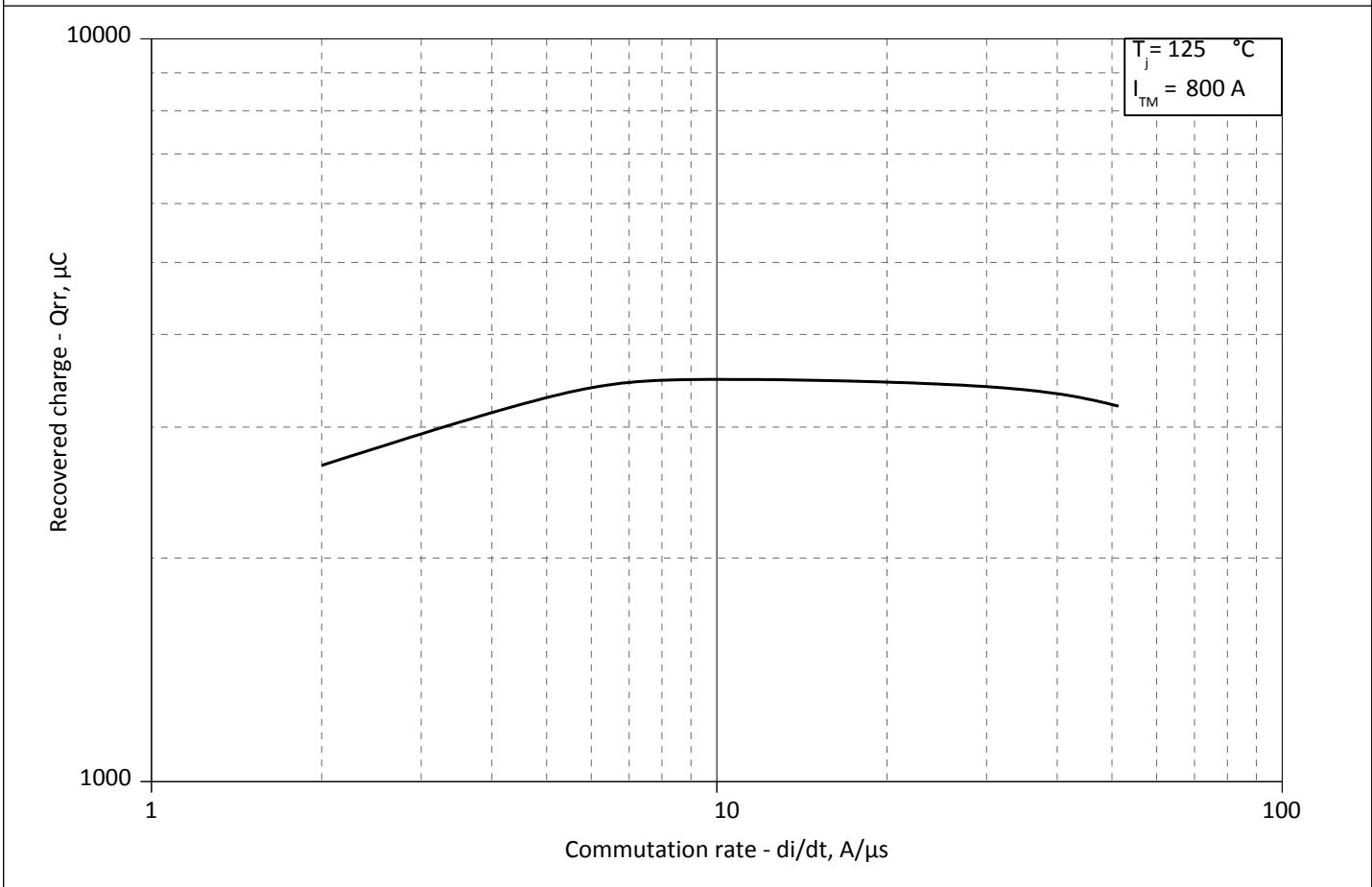


Fig 4 – Maximum recovered charge Q_{rr} vs. commutation rate di_r/dt (25% chord)

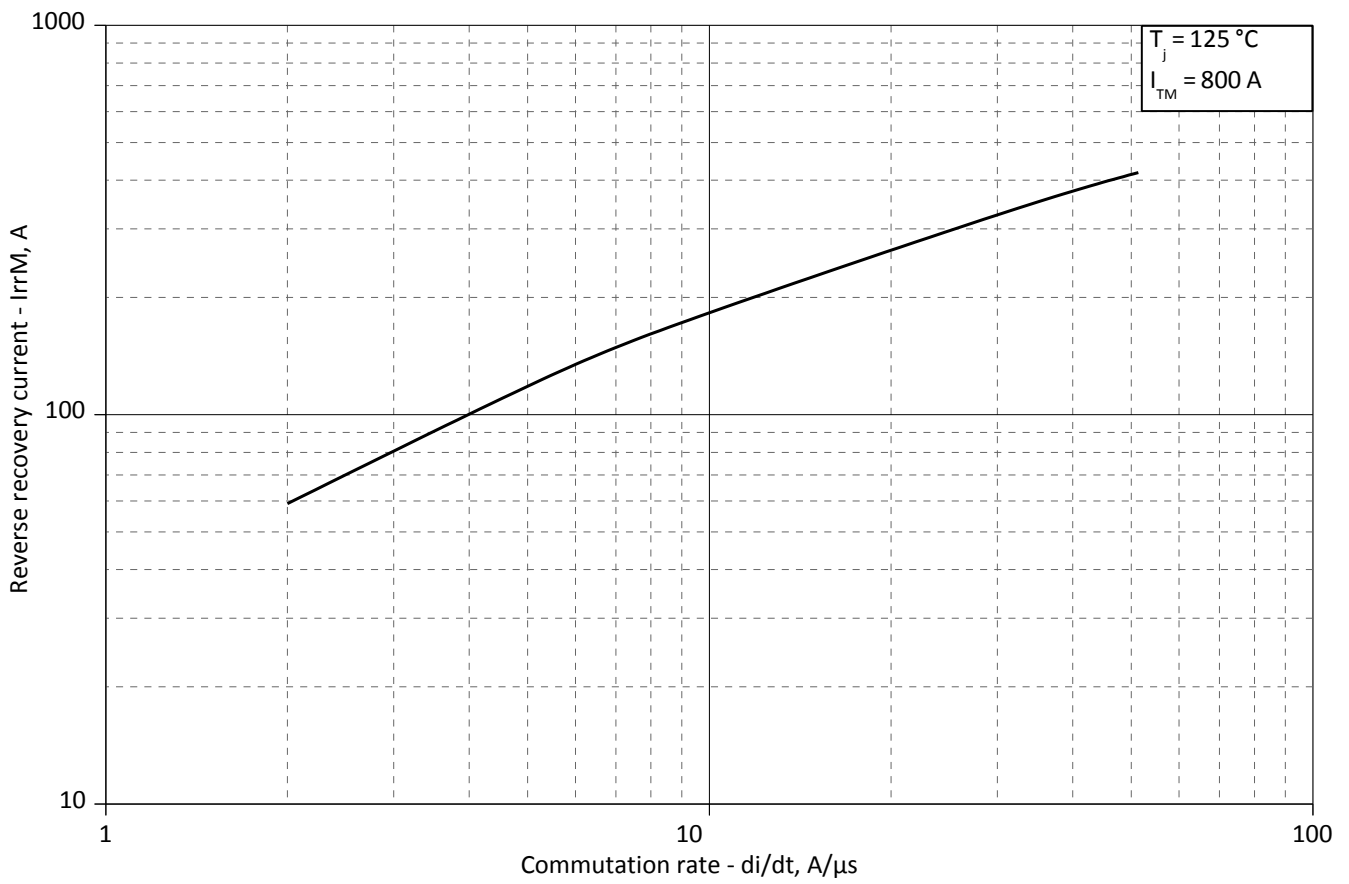


Fig 5 – Maximum reverse recovery current I_{rM} vs. commutation rate di_r/dt

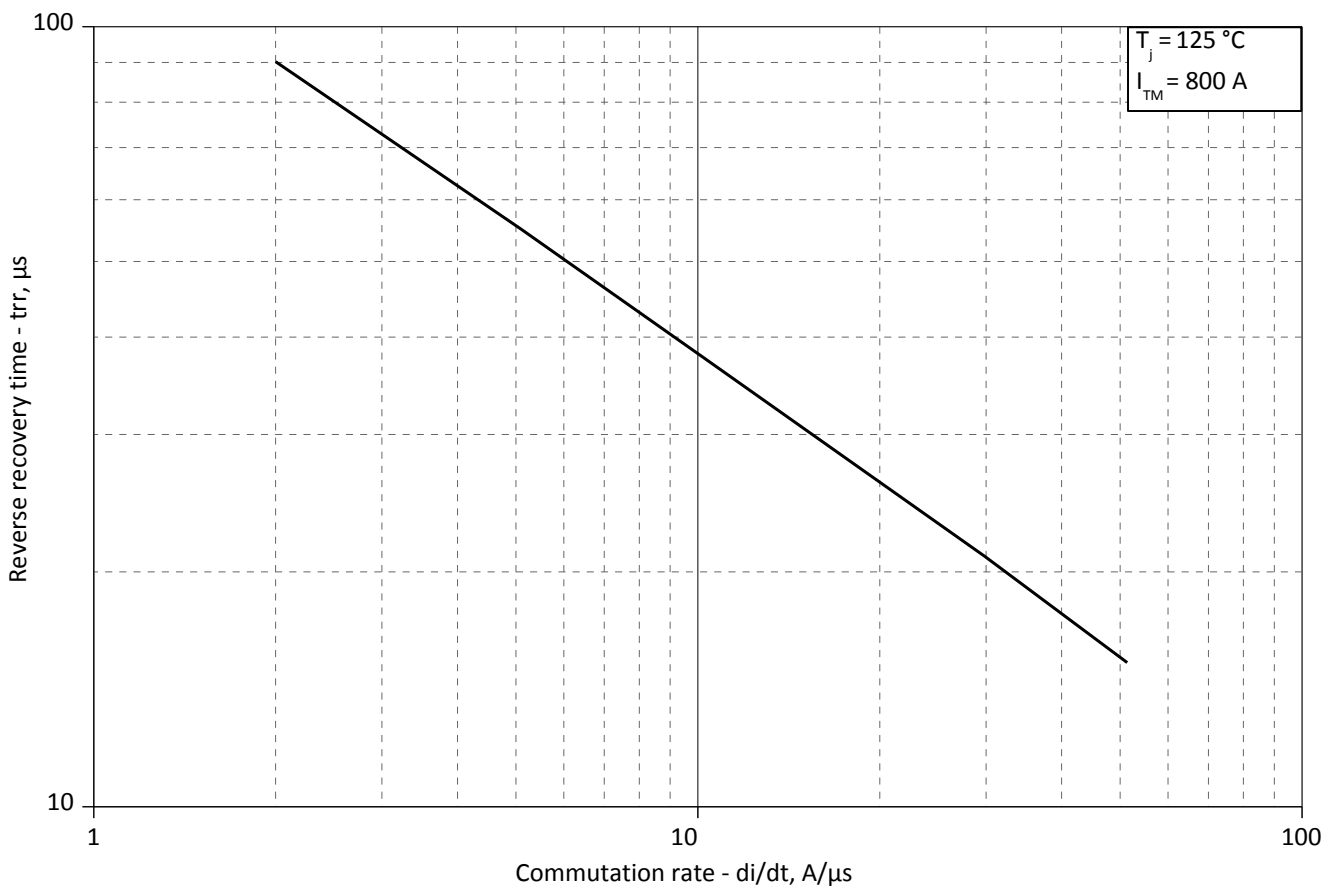


Fig 6 – Maximum recovery time t_r vs. commutation rate di_r/dt (25% chord)

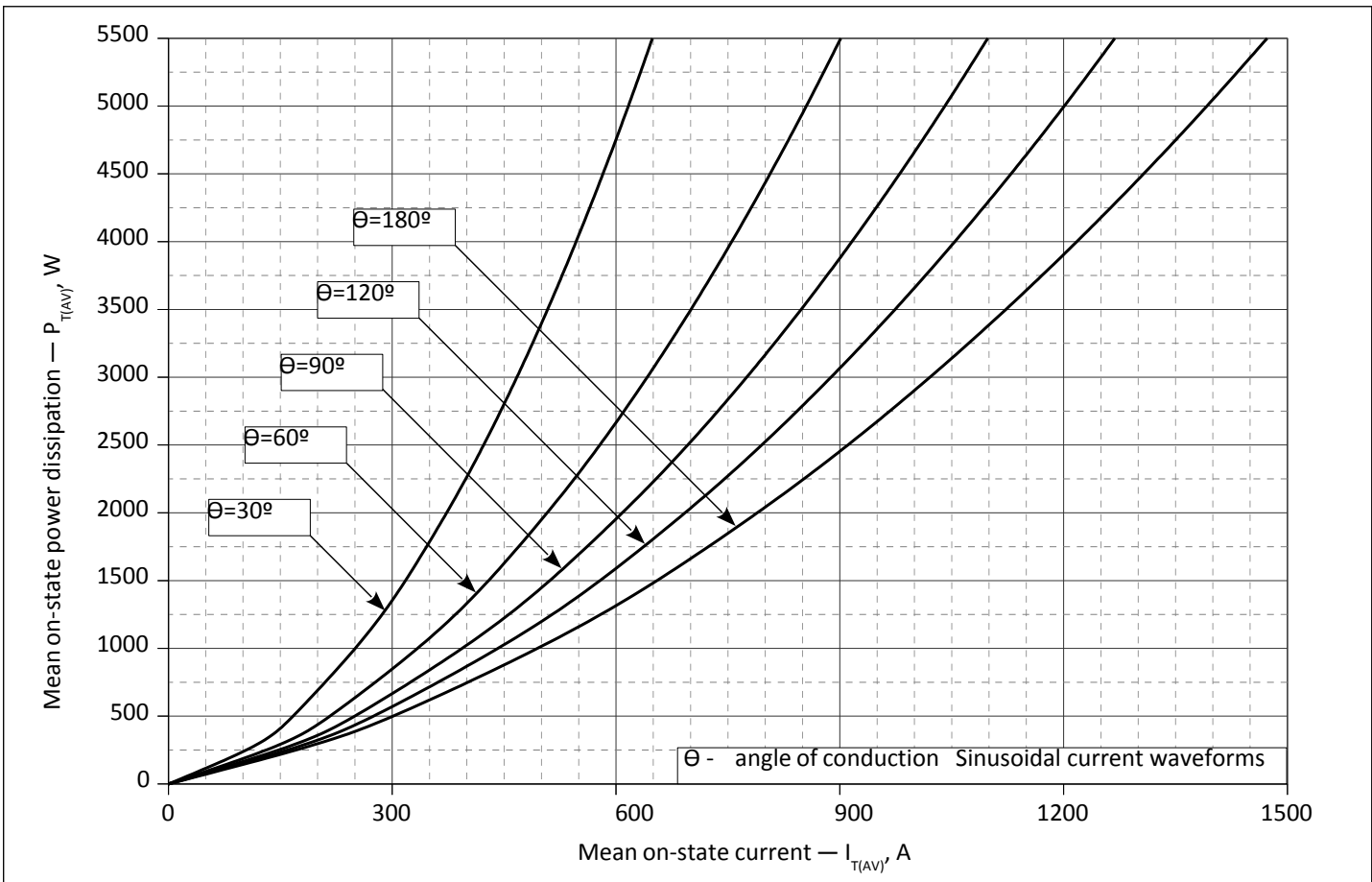


Fig. 7 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

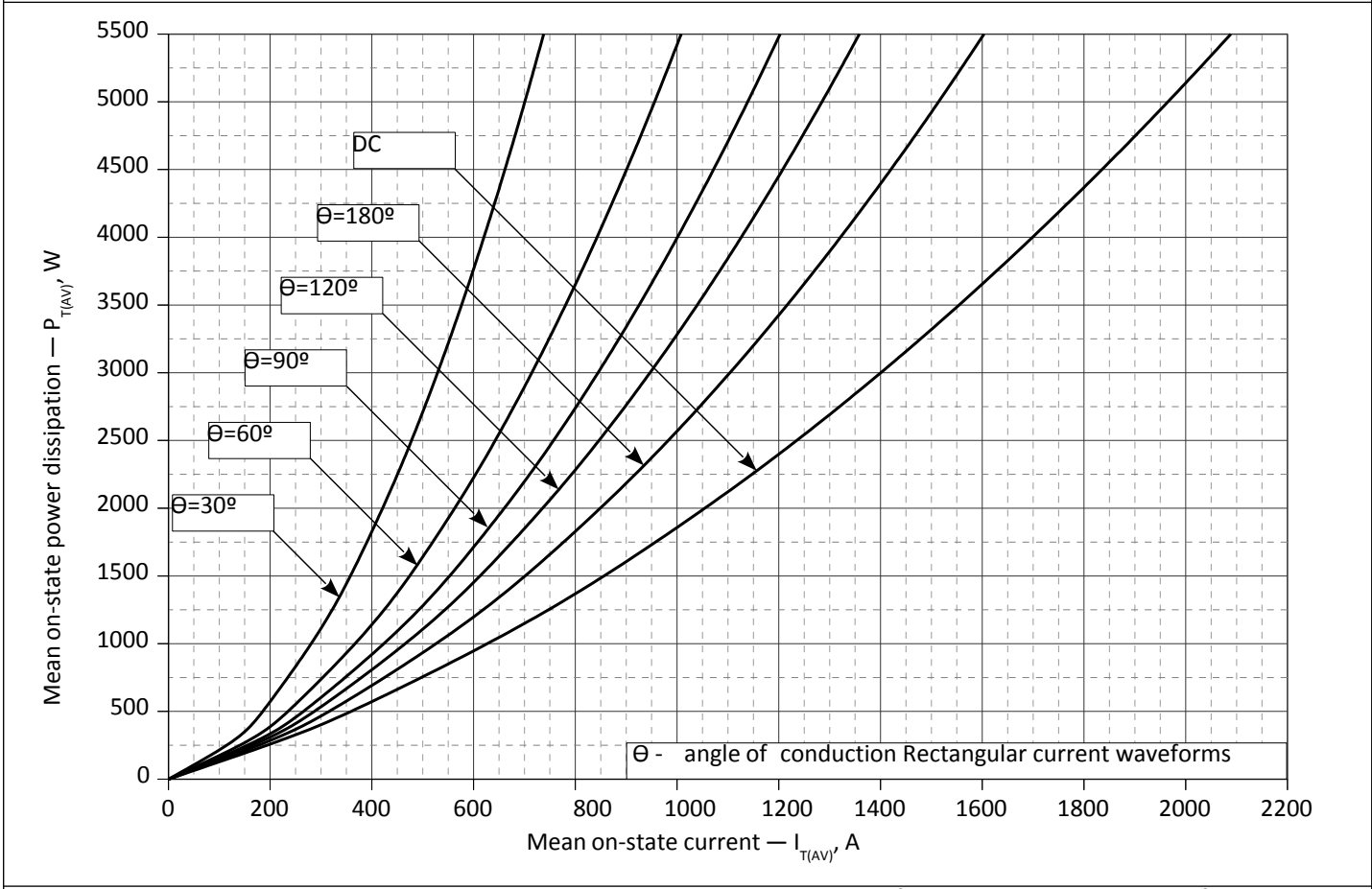


Fig. 8 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

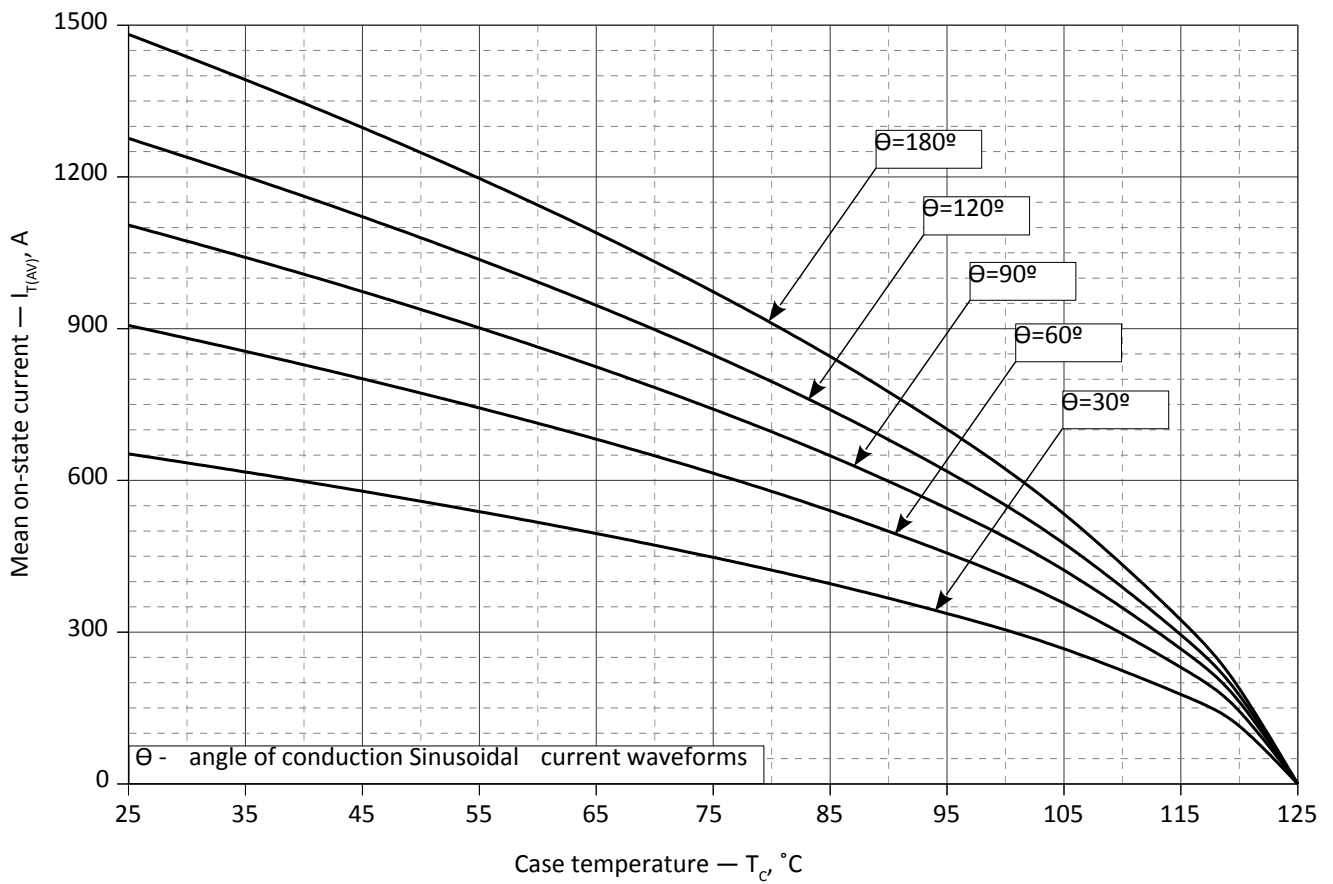


Fig. 9 – Mean on-state current $I_{T(AV)}$ vs. case temperature T_c for sinusoidal current waveforms at different conduction angles (f=50Hz, DSC)

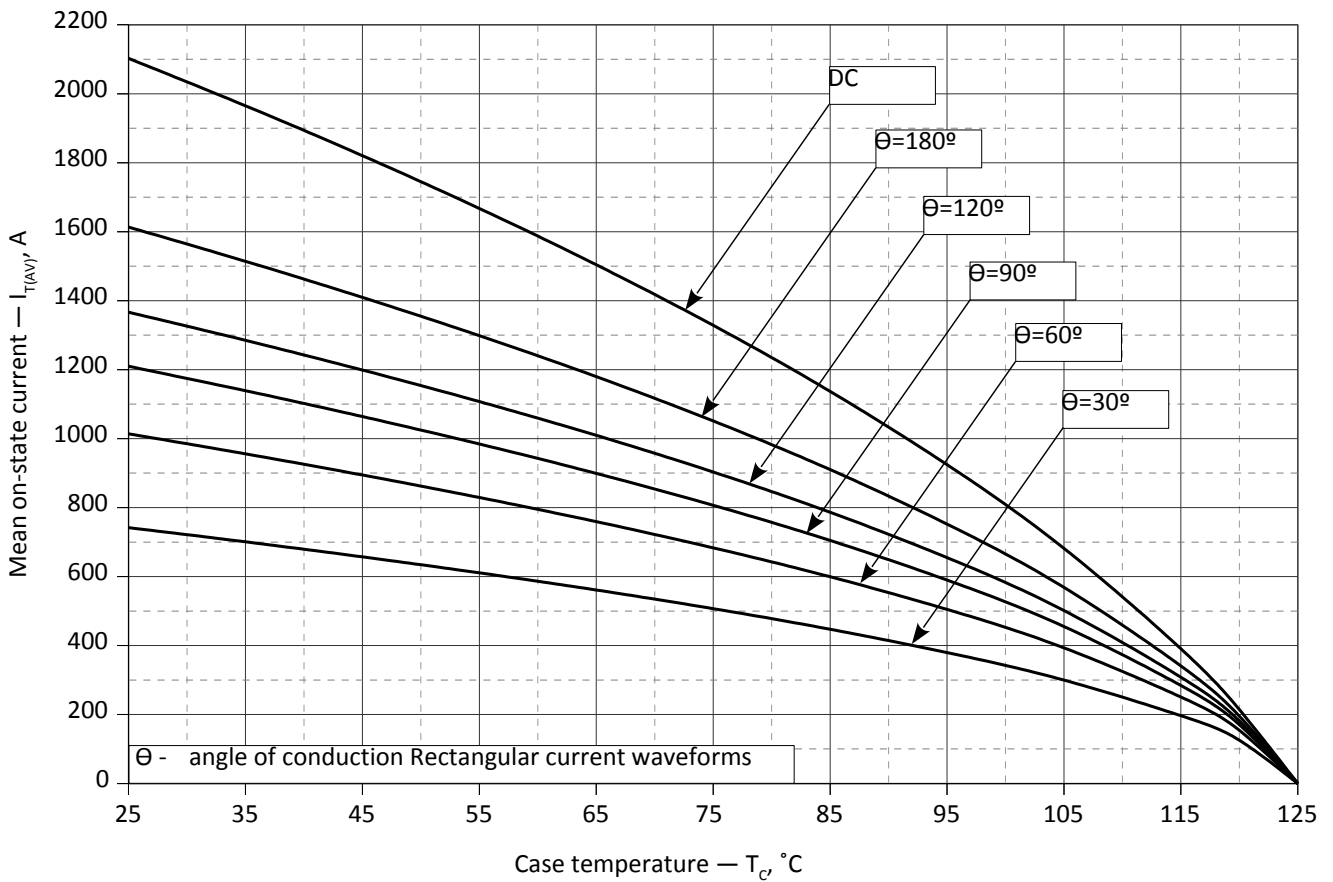


Fig. 10 - Mean on-state current $I_{T(AV)}$ vs. case temperature T_c for rectangular current waveforms at different conduction angles and for DC (f=50Hz, DSC)

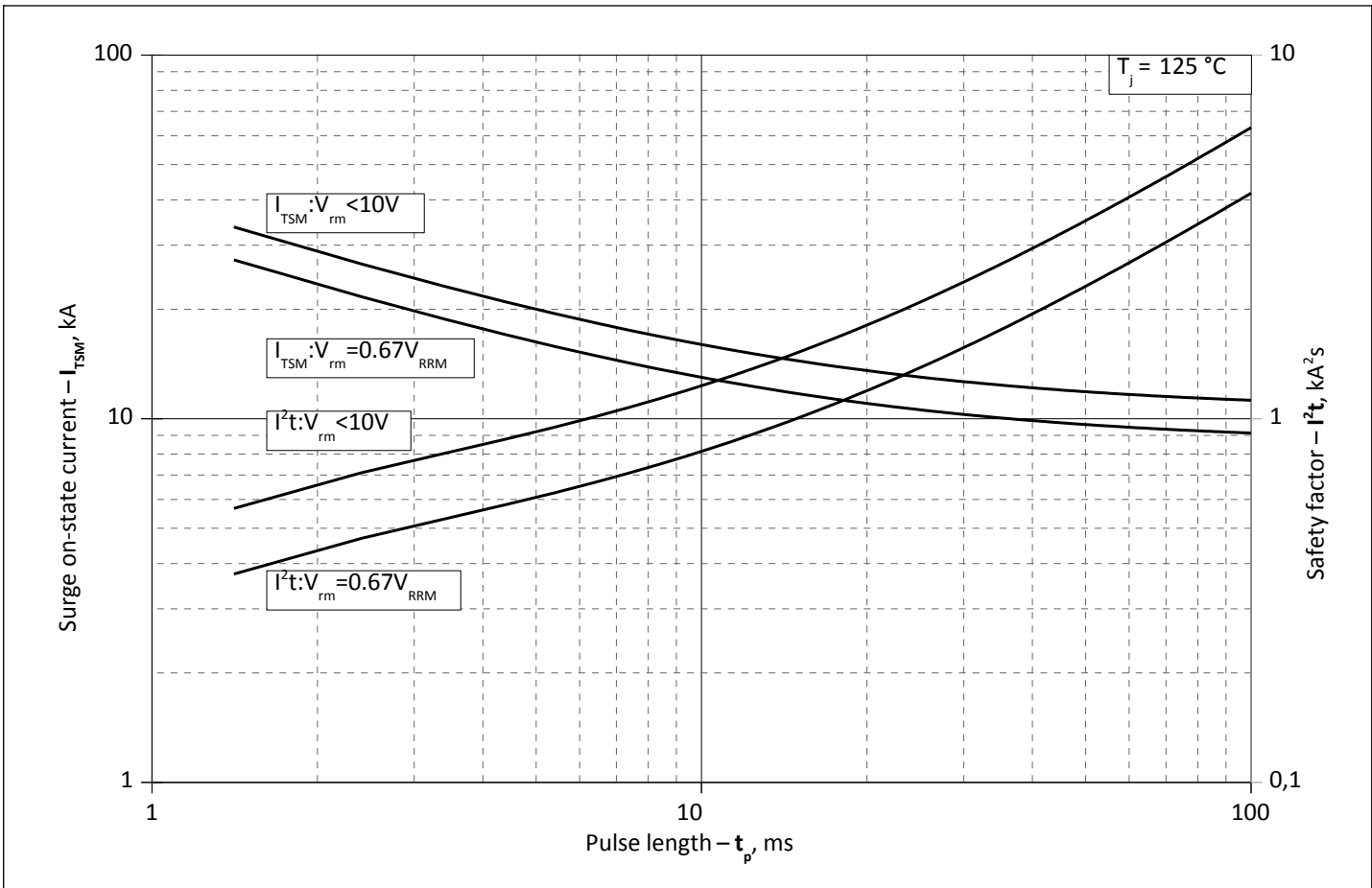


Fig. 11 – Maximum surge on-state current I_{TSM} and safety factor I^2t vs. pulse length t_p

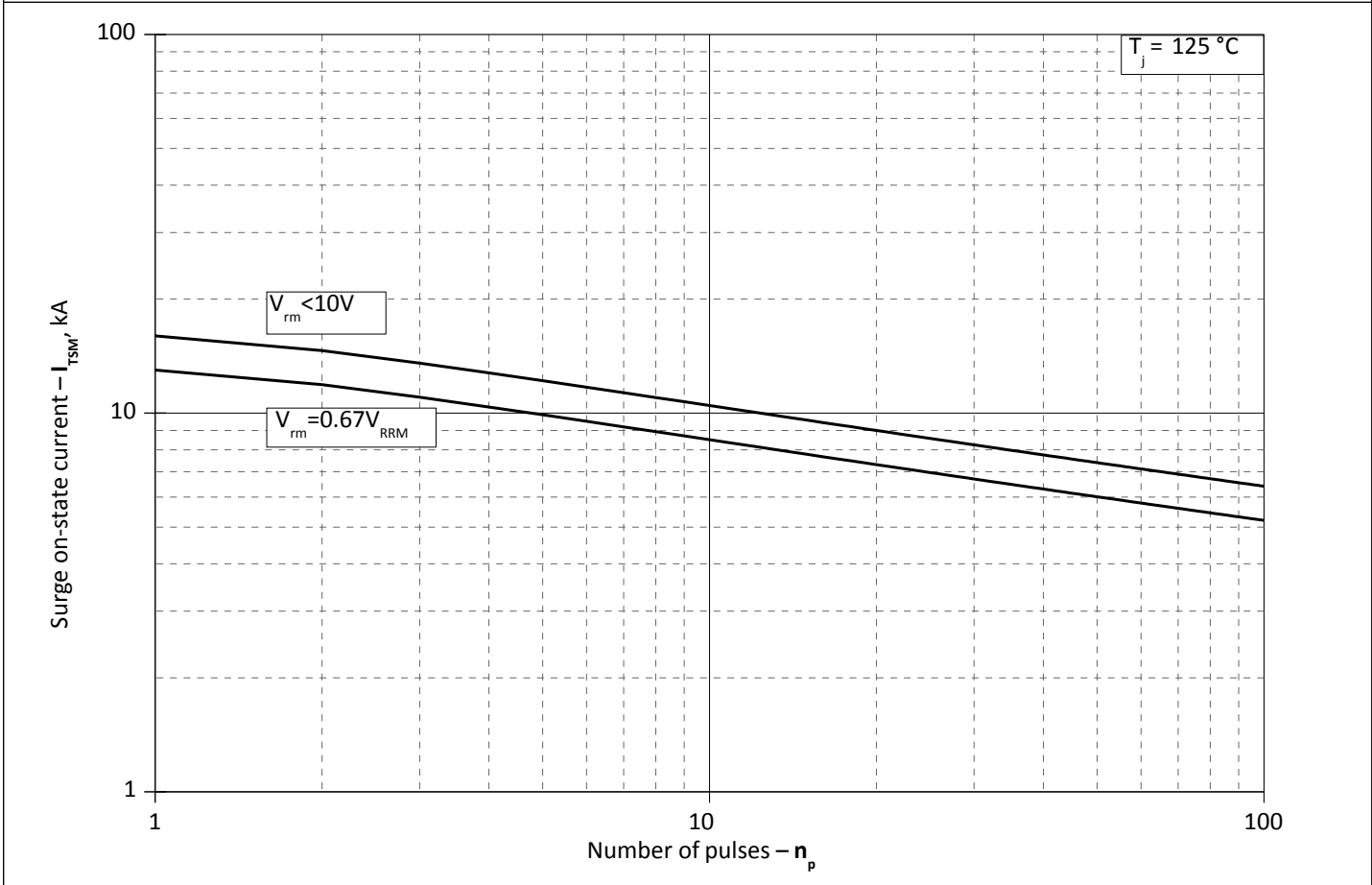


Fig. 12 - Maximum surge on-state current I_{TSM} vs. number of pulses n_p